BUK9K29-100E

Dual N-channel TrenchMOS logic level FET

28 March 2013

Product data sheet

1. General description

Dual logic level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} > 0.5 V @ 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V	
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	30	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	68	W	
Tj	junction temperature			-55	-	175	°C	
Static characte	Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 12$		-	25.1	29	mΩ	
Dynamic characteristics FET1 and FET2								
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 80 V; V _{GS} = 10 V;		-	54	-	nC	
Q _{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	10.9	-	nC	

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche Ruggedness FET1 and FET2							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 30 A; $V_{sup} \le 100 \text{ V}$; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; Fig. 3	[1][2]	-	-	83	mJ

- [1] Refer to application note AN10273 for further information
 [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	1 2 3 4	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	(GGT1200)	

Ordering information

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
BUK9K29-100E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

Marking

Table 4. Marking codes

Type number	Marking code
BUK9K29-100E	9291E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	R _{GS} = 20 kΩ; $T_j \ge 25$ °C; $T_j \le 175$ °C		-	100	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	30	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	21	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	118	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	68	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode FET1 and FET2	,			'	
I _S	source current	T _{mb} = 25 °C		-	30	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	118	Α
Avalanche	Ruggedness FET1 and FET2	,			,	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 30 \text{ A; } V_{sup} \le 100 \text{ V; } V_{GS} = 5 \text{ V;}$ $T_{j(init)} = 25 \text{ °C; } Fig. 3$	[3][4]	-	83	mJ
		V				

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}.
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

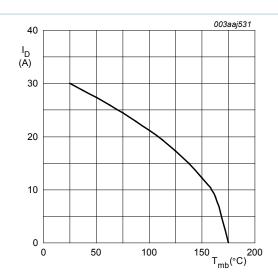


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

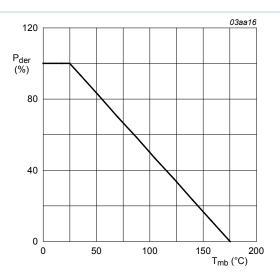


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$$

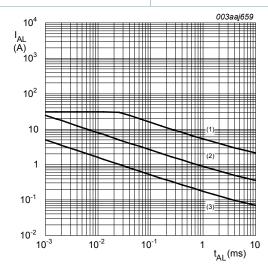


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse; $T_j = 25 \,^{\circ}C$.
- (2) Single-pulse; $T_j = 150 \,^{\circ}C$.
 - (3) Repetitive.

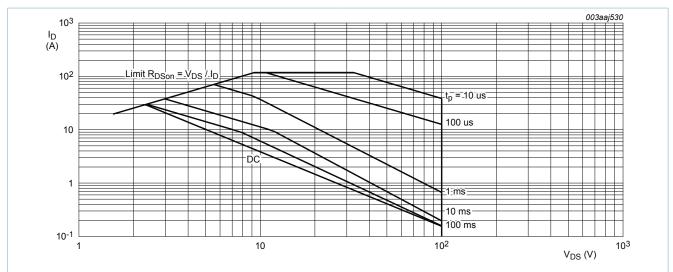


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.21	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

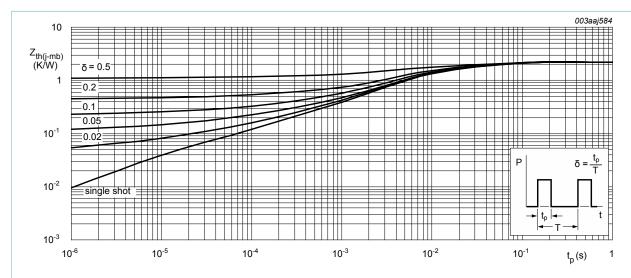


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics FET1 and FET2		'			
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon} drain-source on-staresistance	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	25.1	29	mΩ
	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 12; Fig. 13	-	68.02	80	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	22.7	27	mΩ
Dynamic c	haracteristics FET1 and FE	T2				
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	54	-	nC
Q_{GS}	gate-source charge	I _D = 10 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 14</u>	-	5.6	-	nC
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	10.9	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	2727	3637	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	169	203	pF
C _{rss}	reverse transfer capacitance		-	106	145	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_{L} = 8 Ω ; V_{GS} = 10 V;	-	6.1	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 10 A$	-	6.4	-	ns
t _{d(off)}	turn-off delay time		-	67.3	-	ns
t _f	fall time		-	35.1	-	ns
Source-dra	ain diode FET1 and FET2			1	1	
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 17</u>	_	0.78	1.2	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	32.7	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$	-	50.1	-	nC

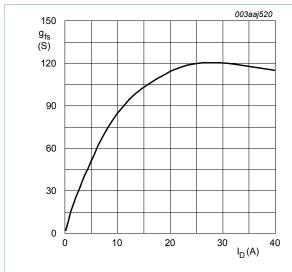


Fig. 6. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$$

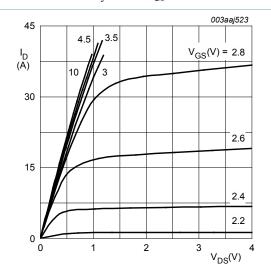


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j=25\,^{\circ}C$$

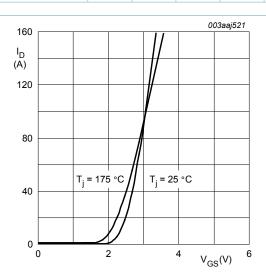


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

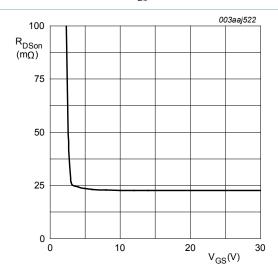


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; \ I_D = 5A$$

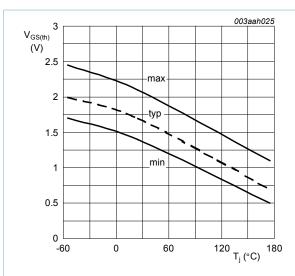


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$

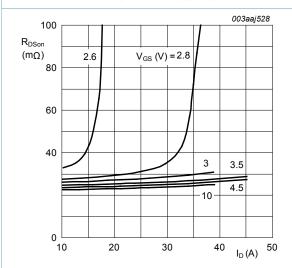


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

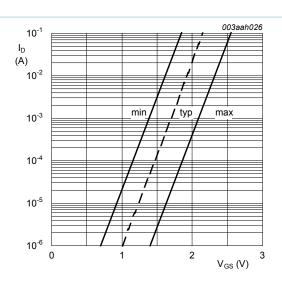


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

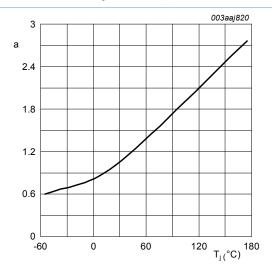


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon} \cos \alpha}$$

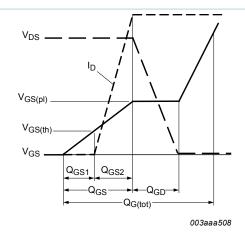


Fig. 14. Gate charge waveform definitions

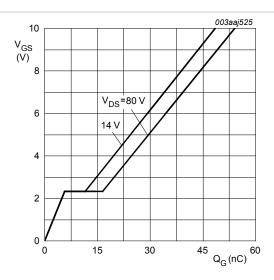


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 10A$$

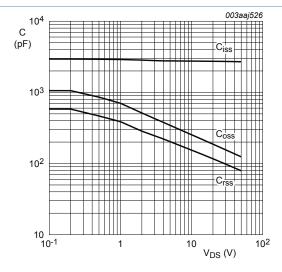


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{\mathit{GS}}\!=\!\mathbf{0}\,V; f=\!\mathbf{1}MHz$$

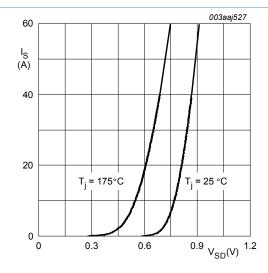
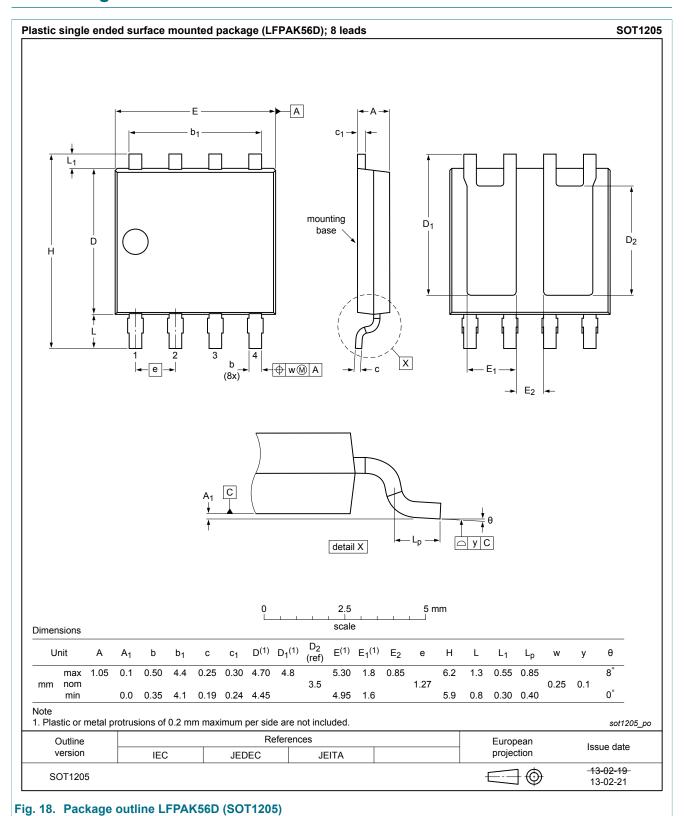


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

11. Package outline



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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